

Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
	0.032 at V _{GS} = - 4.5 V	- 5.3		
- 12	0.042 at V _{GS} = - 2.5 V	- 4.6		
	0.059 at V _{GS} = - 1.8 V	- 3.9		

FEATURES

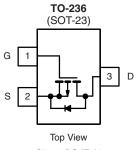
- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFET

APPLICATIONS

- Load Switch
- PA Switch



RoHS COMPLIANT HALOGEN FREE Available



Si2333DS (E3)* * Marking Code

Ordering Information: Si2333DS-T1-E3 (Lead (Pb)-free) Si2333DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	r _A = 25 °C, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T 150 °C)ª. b	T _A = 25 °C	- I _D	- 5.3	- 4.1	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		- 4.2	- 3.3	•
Pulsed Drain Current		I _{DM}	- 20		А
Continuous Source Current (Diode Conduction) ^{a, b}		۱ _S	- 1.0	- 0.6	
Maximum Dississional b	T _A = 25 °C	P _D	1.25	0.75	W
Maximum Power Dissipation ^{a, b}	T _A = 70 °C		0.8	0.48	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marine In the Archive Ia	t ≤ 5 s	R _{thJA}	75	100	
Maximum Junction-to-Ambient ^a	Steady State	''thJA	120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

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			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 12			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 0.40		- 1.0	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA	
Zara Cata Valtaga Drain Currant	1	$V_{DS} = -9.6 V, V_{GS} = 0 V$			- 1	μΑ	
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 9.6 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 20			А	
		V _{GS} = - 4.5 V, I _D = - 5.3 A		0.025	0.032	32	
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 4.6 A		0.033	0.042	Ω	
		V _{GS} = - 1.8 V, I _D = - 2.0 A		0.046	0.059		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 5.3 A		17		S	
Diode Forward Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b	11			J	<u> </u>		
Total Gate Charge	Qg			11.5	18	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = - 6 V, V _{GS} = - 4.5 V I _D ≅ - 5.3 A		1.5			
Gate-Drain Charge	Q _{gd}	$I_{\rm D} = -5.3$ A		3.2		1	
Input Capacitance	C _{iss}			1100		pF	
Output Capacitance	C _{oss}	V_{DS} = - 6 V, V_{GS} = 0 V, f = 1 MHz		390			
Reverse Transfer Capacitance	C _{rss}			300			
Switching ^c	<u> </u>						
	t _{d(on)}			25	40		
Turn-On Time	t _r	$V_{DD} = -6 \text{ V}, \text{ R}_{L} = 6 \Omega$		45	70		
T 0// T	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V R _G = 6 Ω		72	110	ns	
Turn-Off Time	t _f	16 - 0 22		60	90	1	

Notes:

a. Pulse test: PW \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. For design aid only, not subject to production testing.

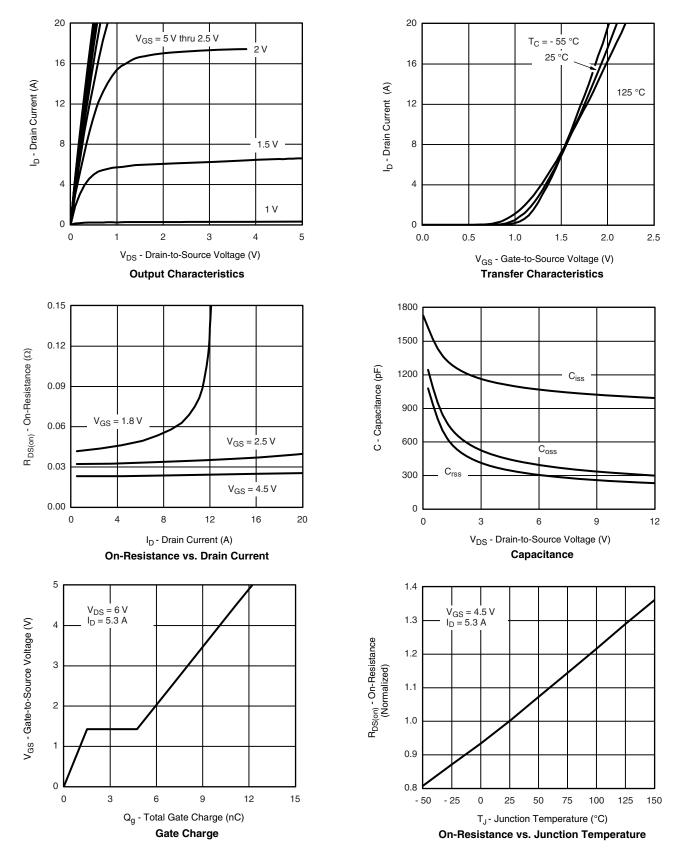
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



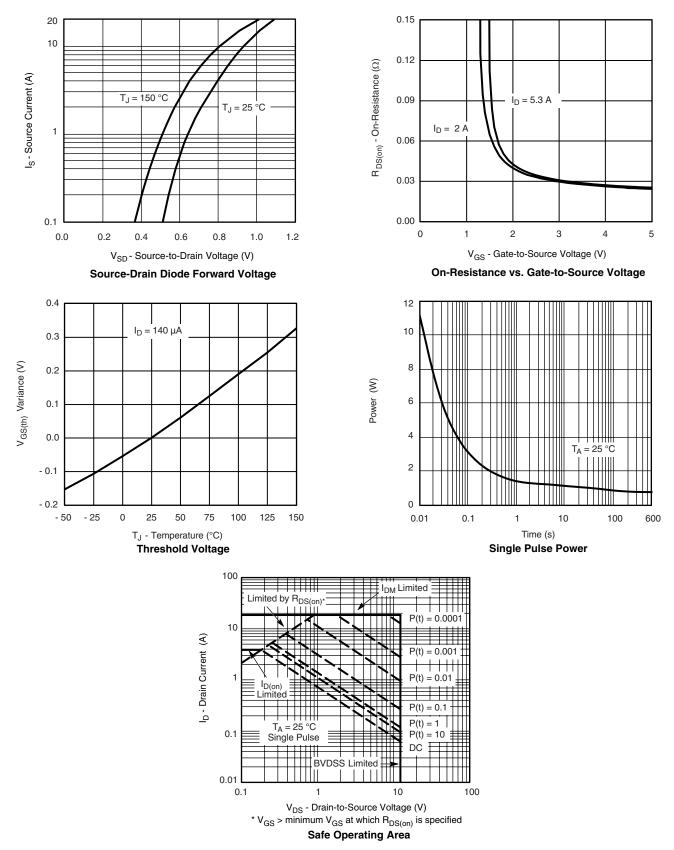
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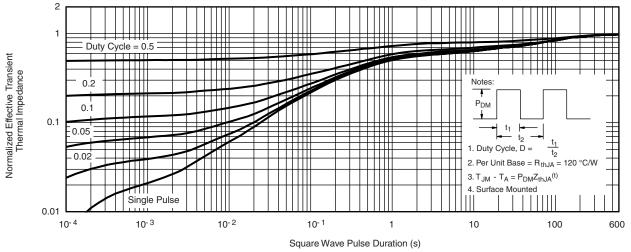
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72023.



Package Information

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SOT-23 (TO-236): 3-LEAD







Dim -	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	



Application Note 826

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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